



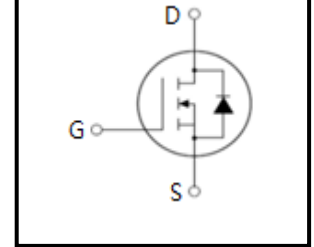
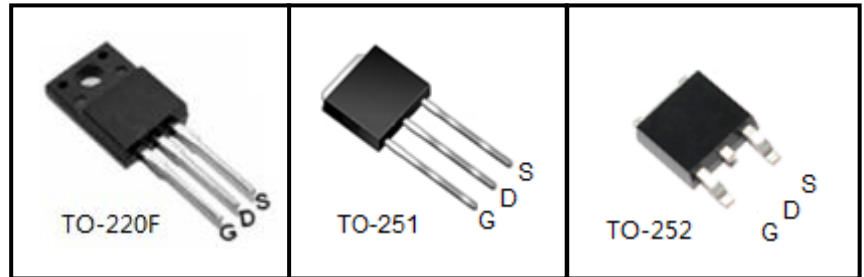
600V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
TMA2N60H	TO-220F	A2N60H
TMU2N60H	TO-251	U2N60H
TMD2N60H	TO-252	D2N60H

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value			Unit
		TO-220F	TO-251	TO-252	
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	600			V
Continuous Drain Current	I_D	2			A
Pulsed Drain Current (note1)	I_{DM}	8			A
Gate-Source Voltage	V_{GSS}	± 30			V
Single Pulse Avalanche Energy (note2)	E_{AS}	57			mJ
Avalanche Current (note1)	I_{AR}	2.4			A
Repetitive Avalanche Energy (note1)	E_{AR}	6.4			mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	20	25		W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150			$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit
		TO-220F	TO-251	TO-252	
Thermal Resistance, Junction-to-Case	R_{thJC}	6.25	5		$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	60		



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.0A$	--	3.5	4.2	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	310	--	pF
Output Capacitance	C_{oss}		--	39	--	
Reverse Transfer Capacitance	C_{rss}		--	6	--	
Total Gate Charge	Q_g	$V_{DD} = 480V, I_D = 2.0A,$ $V_{GS} = 10V$	--	8.0	--	nC
Gate-Source Charge	Q_{gs}		--	1.2	--	
Gate-Drain Charge	Q_{gd}		--	5.0	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 250V, I_D = 2.0A,$ $R_G = 25\Omega$	--	7.8	--	ns
Turn-on Rise Time	t_r		--	33	--	
Turn-off Delay Time	$t_{d(off)}$		--	23	--	
Turn-off Fall Time	t_f		--	59	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	2	A
Pulsed Diode Forward Current	I_{SM}		--	--	8	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 2.0A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 2.0A,$ $di_F/dt = 100A/\mu s$	--	80	--	ns
Reverse Recovery Charge	Q_{rr}		--	1.8	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 2.4A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

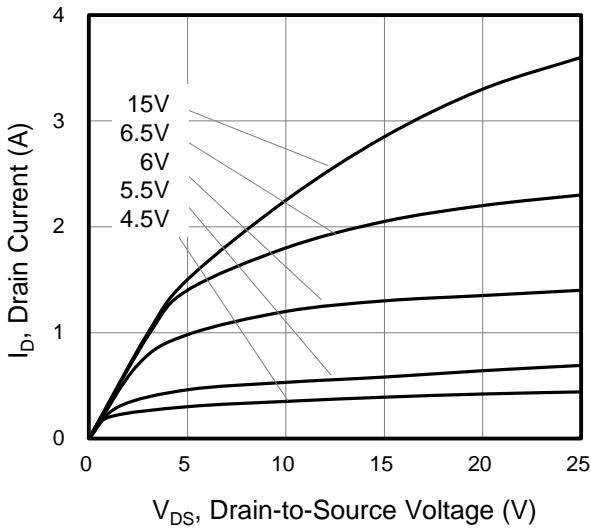


Figure 2. Body Diode Forward Voltage

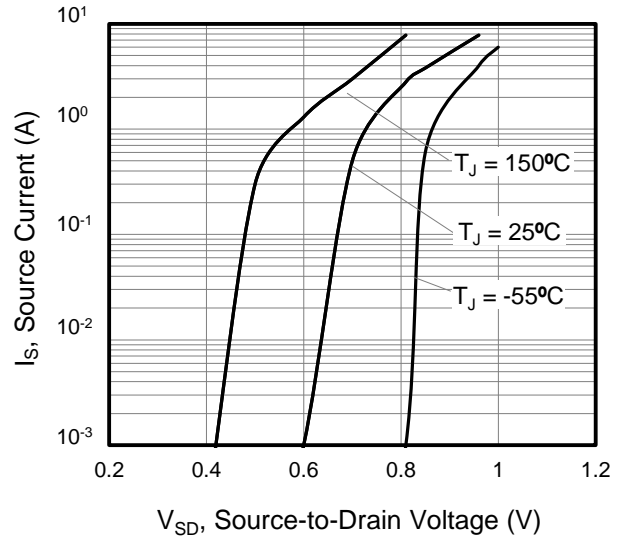


Figure 3. Drain Current vs. Temperature

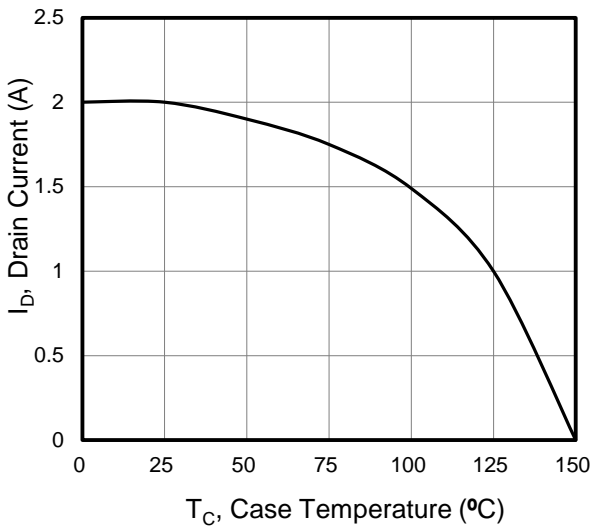


Figure 4. Power Dissipation vs. Temperature
TO-251, TO-252

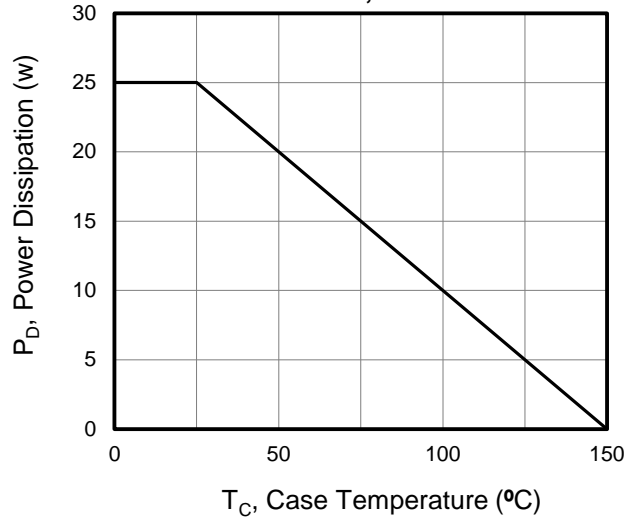


Figure 5. Transfer Characteristics

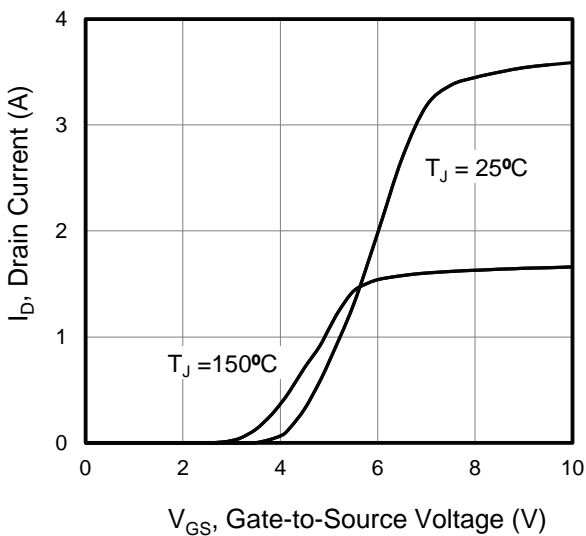
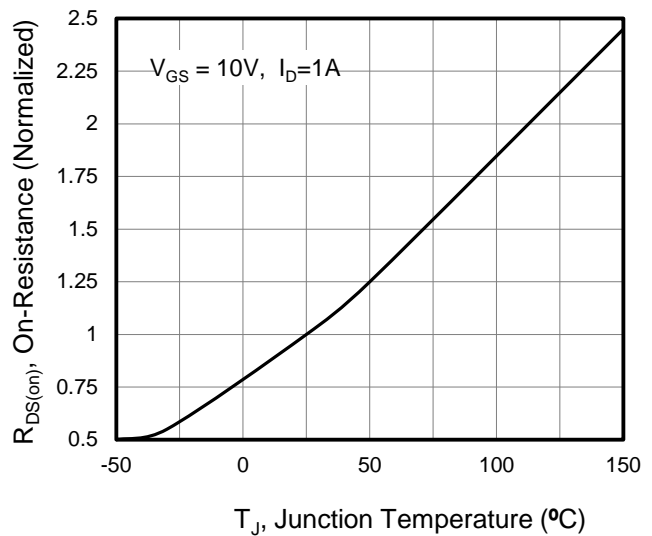


Figure 6. On-Resistance vs. Temperature





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

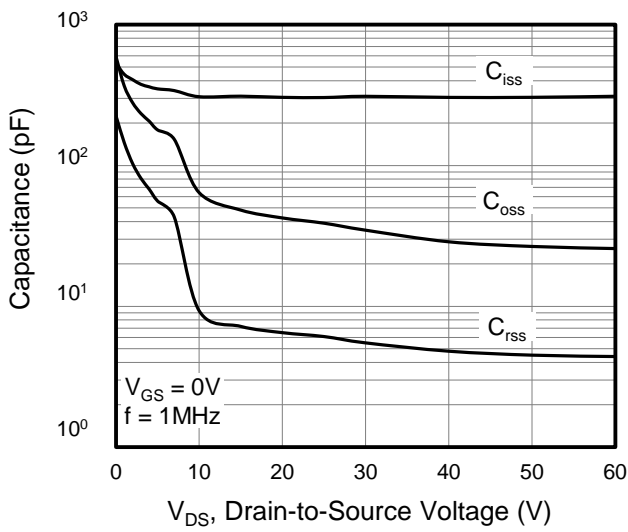


Figure 8. Gate Charge

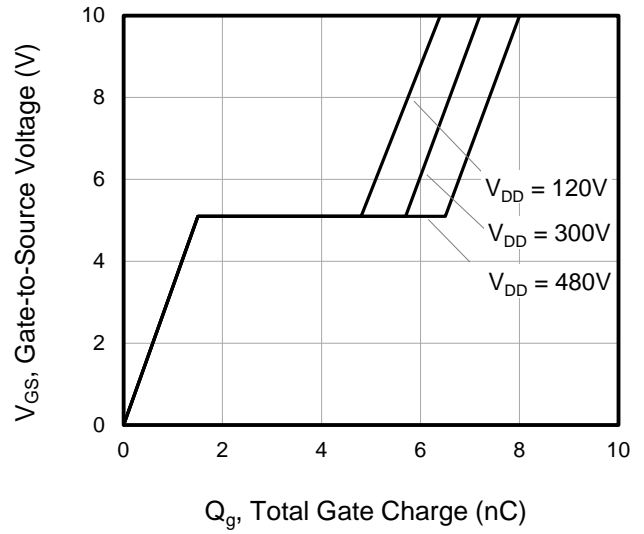


Figure 9. Transient Thermal Impedance TO-251, TO-252

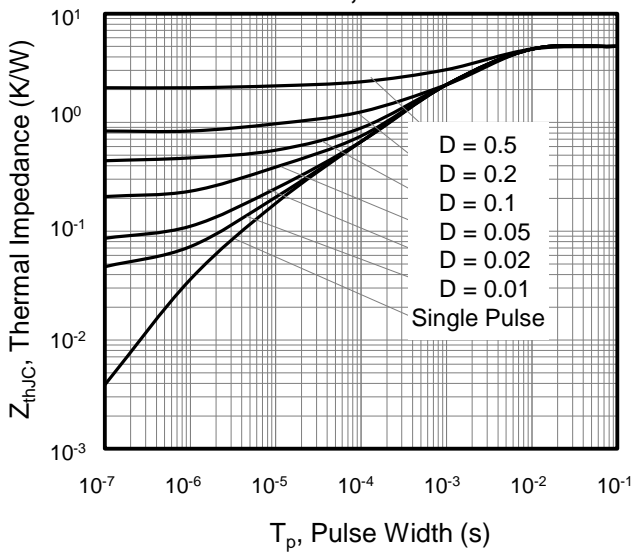


Figure 10. Transient Thermal Impedance TO-220F

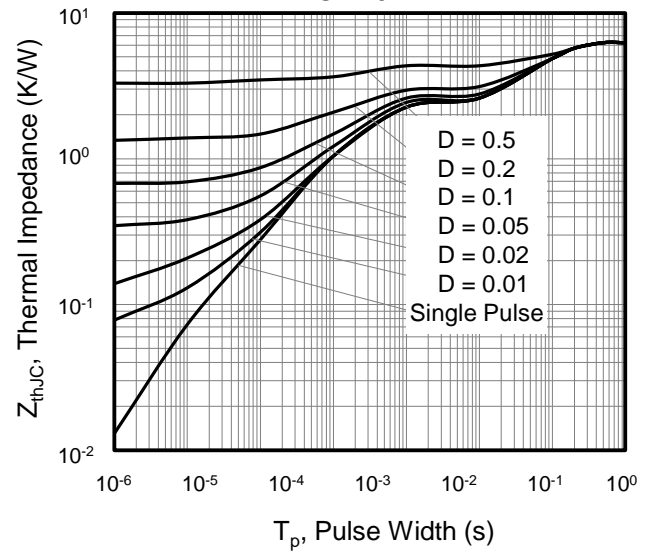




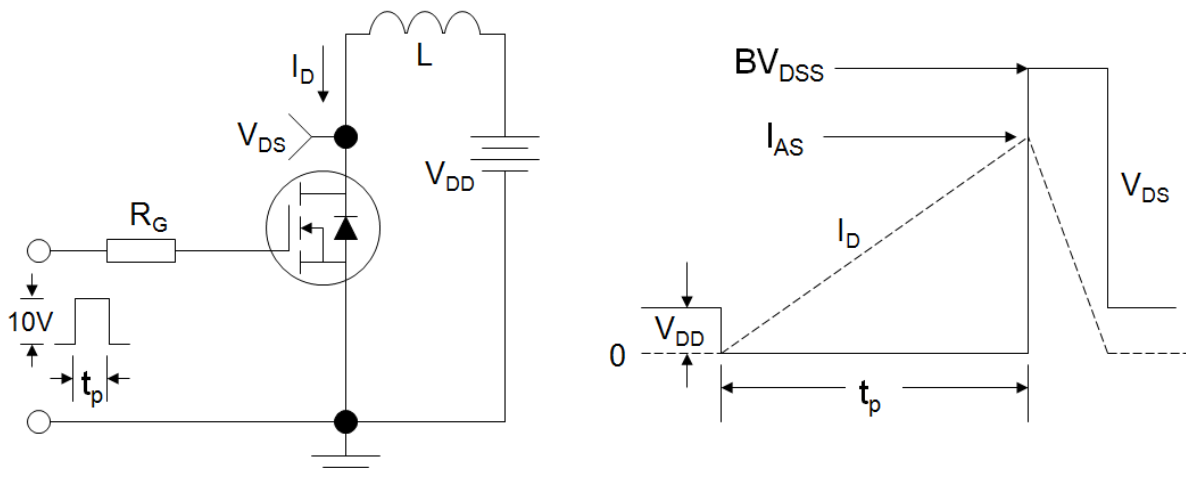
Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

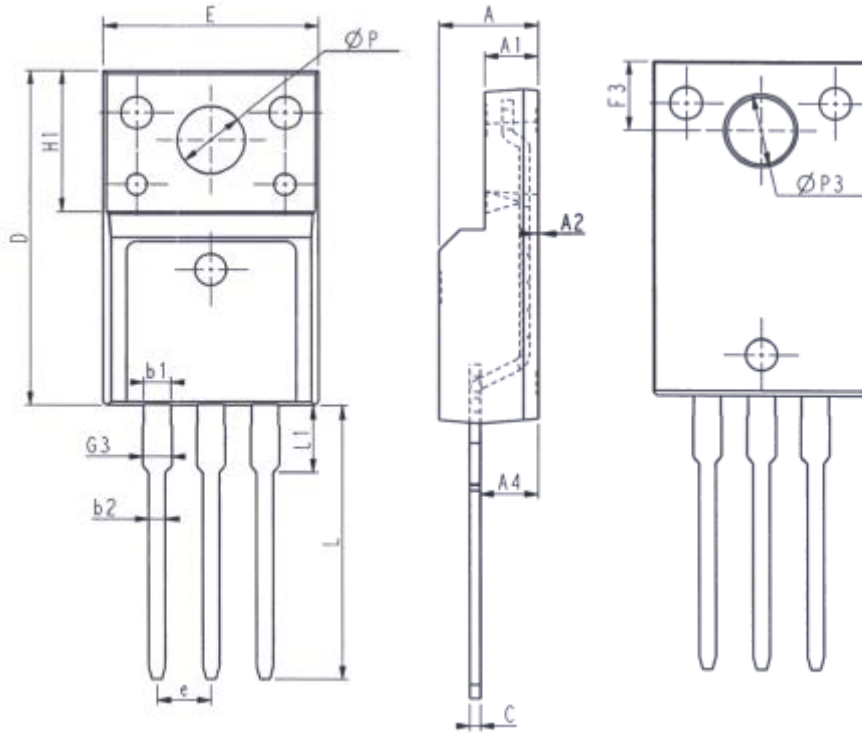


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





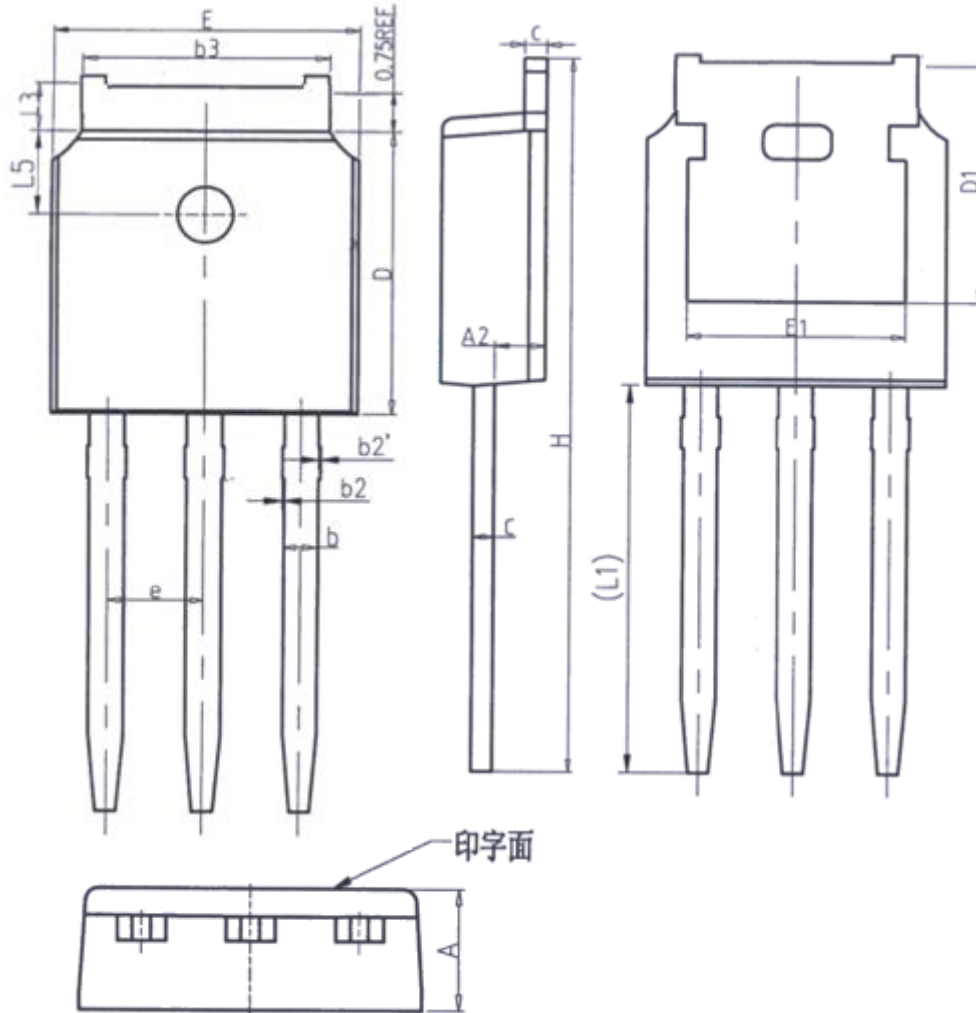
TO-220F



Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12.68	13.28
A	4.50	4.90	L1	2.93	3.13
A1	2.34	2.74	P	3.03	3.38
A2	0.30	0.60	P3	3.15	3.65
A4	2.56	2.96	F3	3.15	3.45
c	0.40	0.65	G3	1.25	1.55
D	15.57	16.17	b1	1.18	1.43
H1	6.70REF		b2	0.70	0.95
e	2.54BSC				



TO-251

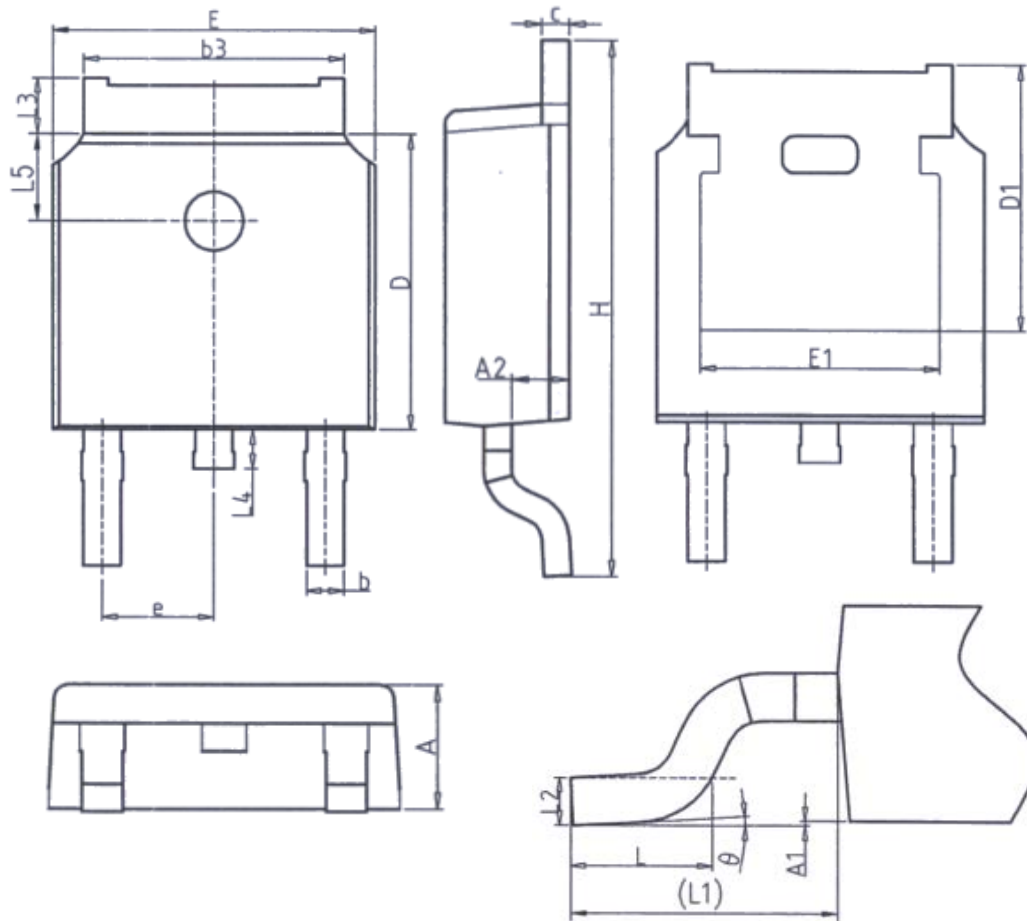


Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2'	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95



TO-252



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	-

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	-	1.00
L5	1.65	1.95
theta	0°	8°



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